

Datasheet

FS8205

Dual N-Channel Enhancement Mode Power MOSFET

FORTUNE,
Properties
For Reference Only

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1. Features

1.1 Low on-resistance

1.1.1 $R_{DS(ON)} = 28\text{ m}\Omega$ MAX. ($V_{GS} = 4.5\text{V}$, $I_D = 4\text{A}$)

1.1.2 $R_{DS(ON)} = 37\text{ m}\Omega$ MAX. ($V_{GS} = 2.5\text{V}$, $I_D = 3\text{A}$)

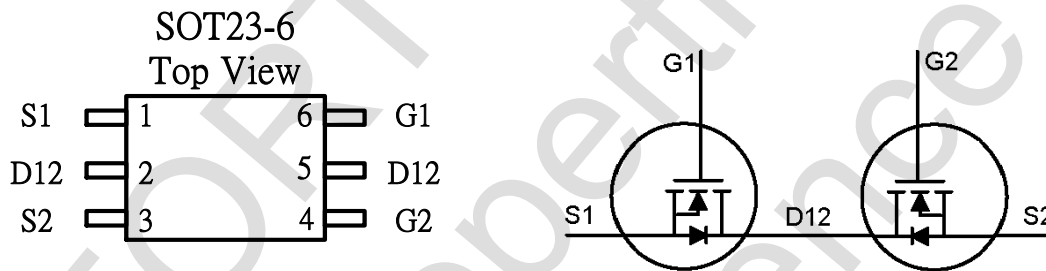
2. Applications

- Li-ion battery management applications

3. Ordering Information

Product Number	Description	Package Type	Quantity/Reel
FS8205	SOT23-6 package version	SOT23-6	3,000

4. Pin Assignment



5. Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	20	V
VGS	Gate-Source Voltage	±12	V
ID @TA = 25°C	Continuous Drain Current ³	6	A
ID @TA = 70°C	Continuous Drain Current ³	5	A
IDM	Pulsed Drain Current ¹	25	A
PD @TA = 25°C	Total Power Dissipation	1	W
	Linear Derating Factor	0.008	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

6. Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient ³	Max. 125	°C/W

7. Electrical Characteristics

Electrical Characteristics @T_j = 25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	20	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, $I_D = 1mA$	-	0.1	-	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS} = 4.5V, I_D = 4A$	-	23	28	mΩ
		$V_{GS} = 2.5V, I_D = 3A$	-	30	37	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.45	-	1.2	V
I_{DSS}	Drain-Source Leakage Current ($T_j = 25^\circ C$)	$V_{DS} = 16V, V_{GS} = 0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_j = 70^\circ C$)	$V_{DS} = 16V, V_{GS} = 0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS} = \pm 10V$	-	-	±0.1	μA

8. Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current (Body Diode)	$V_D = V_G = 0V, V_S = 1.2V$	-	-	0.83	A
V_{SD}	Forward On Voltage ²	$T_j = 25^\circ C, I_S = 1.25A, V_{GS} = 0V$	-	-	1.2	V

Notes :

1. Pulse width limited by Max. junction temperature.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Surface mounted on 1 in² copper pad of FR4 board ; 208°C/W when mounted on Min. copper pad.

9. Typical Characteristics

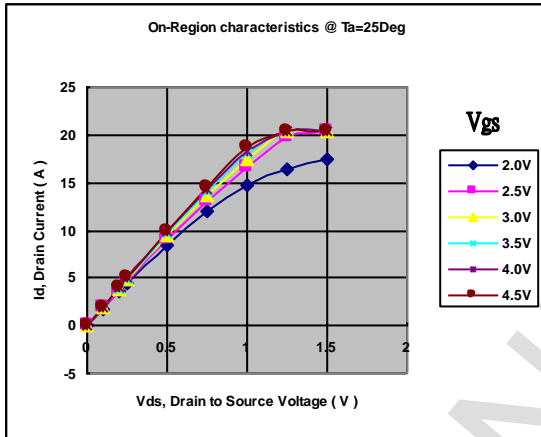


Fig 1. Typical Output Characteristics

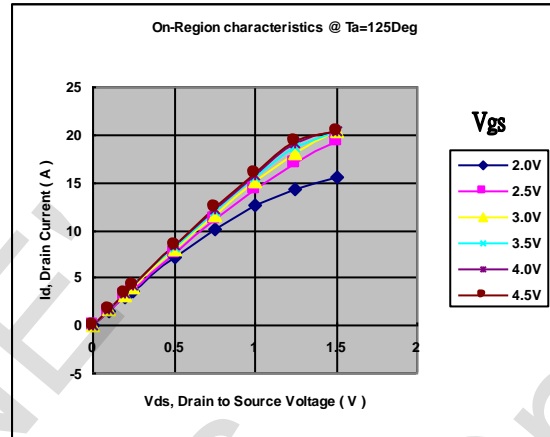


Fig 2. Typical Output Characteristics

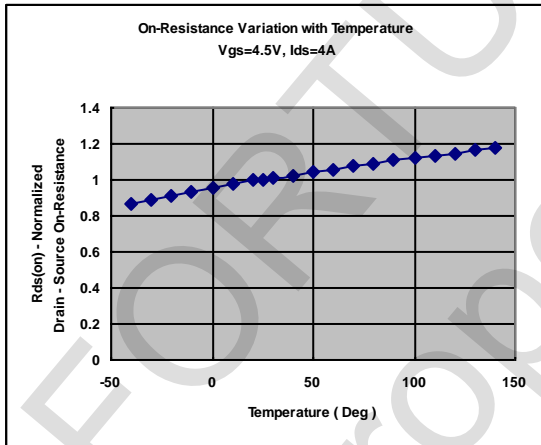


Fig 3. Normalized On-Resistance

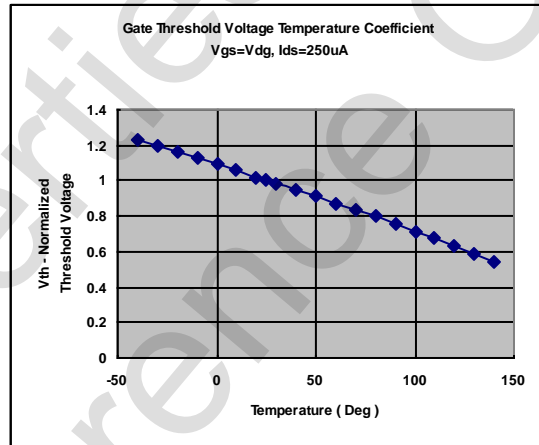


Fig 4. Gate Threshold Variation with Temperature

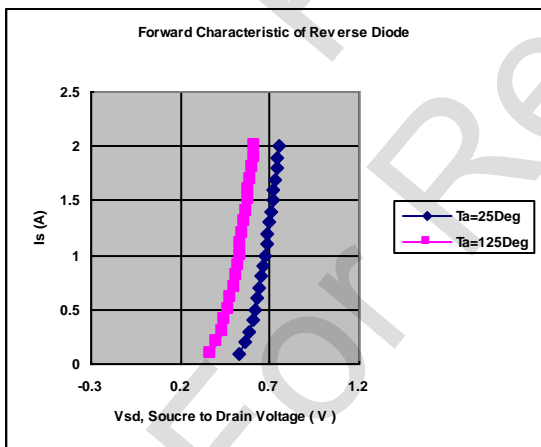
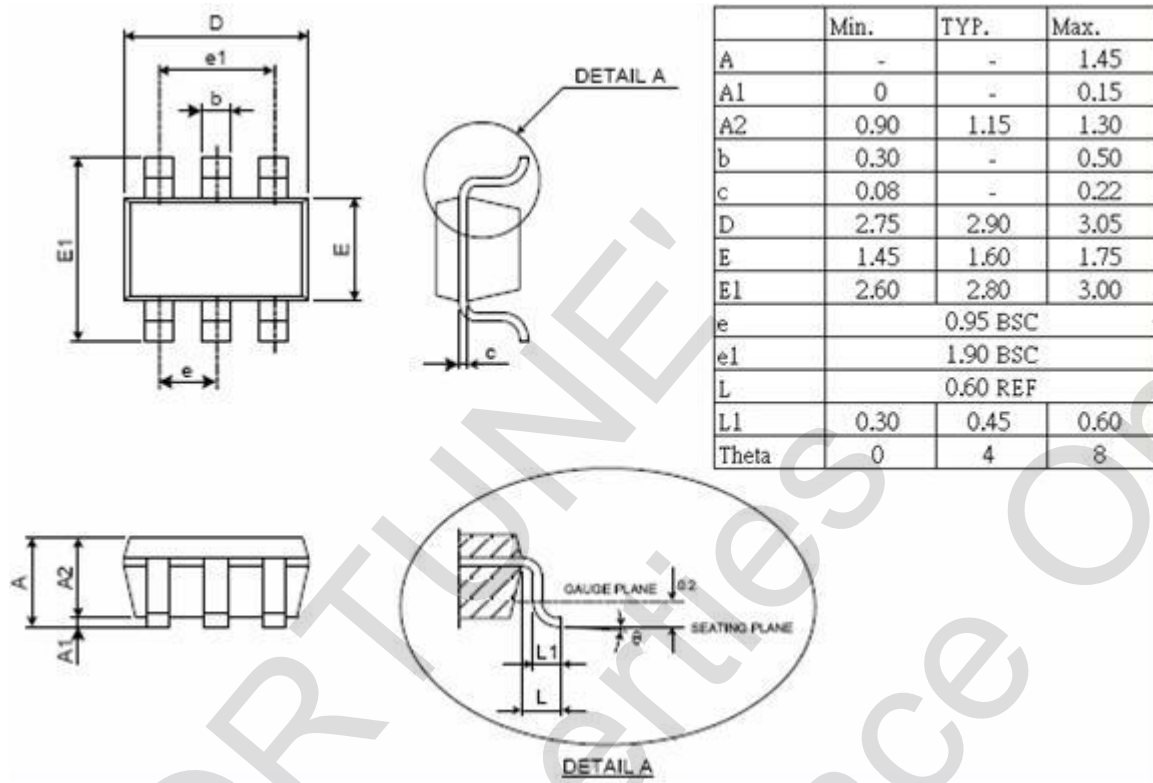


Fig 5. Forward Characteristic of Reverse Diode

10. Package Information



11. Revision History

Version	Date	Page	Description
1.0	2009/08/17	-	Version 1.0 released
1.1	2010/01/26	3	Rds25 TYP 28mohm MAX 36mohm Rds45 TYP 22mohm MAX 26mohm
1.2	2010/06/02	3	Rds45 TYP 23mohm MAX 27mohm
1.3	2010/06/10	4	IDSS Test Conditions : VDS=16V VGS=0V
1.4	2010/08/31	3	Revise Pin Assignment
1.5	2010/04/27	4	Rds25 TYP : 30mohm MAX : 37mohm Rds45 TYP : 23mohm MAX : 28mohm VGS(th) MIN : 0.45V MAX : 1.2V IGSS MAX : ±0.1uA
1.6	2011/09/08	6	Revise Package Outline
1.7	2011/11/02	3	Revise Pin Assignment